

UV-A Sensor GUVV-S10SD

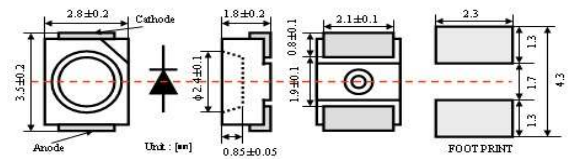


- Features**
- Gallium Nitride Based Material
 - Schottky-type Photodiode
 - Photovoltaic Mode Operation
 - High Responsivity & Low Dark Current



Applications UV-A Lamp Monitoring

Outline Diagrams and Dimensions



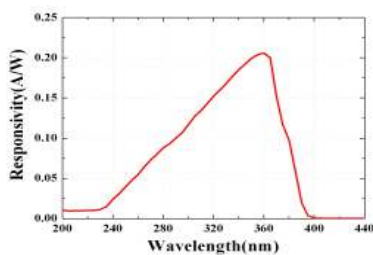
Absolute Maximum Ratings

Parameter	Symbol	Min.	Max.	Unit	Remark
Storage Temperature	T_{st}	-40	90	°C	
Operating Temperature	T_{op}	-30	85	°C	
Reverse Voltage	$V_{r, max.}$		5	V	
Forward Current	$I_{f, max.}$		1	mA	
Soldering Temperature	T_{sol}		260	°C	within 10 sec.

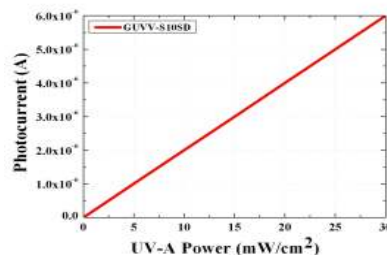
Characteristics (at 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Dark Current	I_d			1	nA	$V_r = 0.1$ V
Photo Current	I_{ph}		200		nA	UVA Lamp, 1 mW/cm^2
Temperature Coefficient	I_{tc}		0.1		%/°C	UVA Lamp
Responsivity	R		0.2		A/W	$\lambda = 360$ nm, $V_r = 0$ V
Spectral Detection Range	λ	240		390	nm	10% of R

Responsivity Curve



Photocurrent along UV Power



Caution